



**THE DATASHEET OF
C3M0040120J1**



C3M0040120J1

Silicon Carbide Power MOSFET
C3M™ MOSFET Technology
N-Channel Enhancement Mode

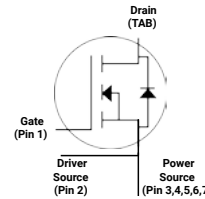


TO-263-7L XL



Features

- 3rd generation SiC MOSFET technology
- Optimized package with separate driver source pin
- High blocking voltage with low on-resistance
- High speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{rr})
- Halogen free, RoHS compliant



Package Types: TO-263-7L XL
PN's: C3M0040120J1

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Applications

- Datacenter and telecom power supplies
- EV battery chargers
- High voltage DC/DC converters
- Energy storage systems
- Solar inverters

Benefits

- Reduce switching losses and minimize gate ringing
- Higher system efficiency
- Reduce cooling requirements
- Increase power density
- Increase system switching frequency

Key Parameters

Parameter	Symbol	Min.	Typ.	Max	Unit	Conditions	Note
Drain - Source Voltage	V_{DS}			1200	V	$T_C = 25^\circ\text{C}$	
Maximum Gate - Source Voltage	$V_{GS(max)}$	-8		+19		Transient	
Operational Gate-Source Voltage	$V_{GS op}$		-4/15			Static	Note 1
DC Continuous Drain Current	I_D			64	A	$V_{GS} = 15\text{ V}, T_C = 25^\circ\text{C}, T_J \leq 150^\circ\text{C}$	Fig. 19 Note 2
				42		$V_{GS} = 15\text{ V}, T_C = 100^\circ\text{C}, T_J \leq 150^\circ\text{C}$	
Pulsed Drain Current	I_{DM}			100		t_{Pmax} limited by T_{Jmax} $V_{GS} = 15\text{ V}, T_C = 25^\circ\text{C}$	Fig. 22
Power Dissipation	P_D			272	W	$T_C = 25^\circ\text{C}, T_J = 150^\circ\text{C}$	Fig. 20
Operating Junction Temperature	T_J			-40 to +175	°C		
Case and Storage Temperature	T_C, T_{stg}			-40 to 150			
Solder Temperature	T_L			260		According to JEDEC J-STD-020	

Note (1): Recommended turn-on gate voltage is 15V with $\pm 5\%$ regulation tolerance, see Application Note PRD-04814 for additional details

Note (2): Verified by design


Electrical Characteristics ($T_C = 25\text{ }^\circ\text{C}$ Unless Otherwise Specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Note
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200				$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.7	3.6	V	$V_{DS} = V_{GS}, I_D = 9.2\text{ mA}$	Fig. 11
			2.2			$V_{DS} = V_{GS}, I_D = 9.2\text{ mA}, T_J = 150\text{ }^\circ\text{C}$	
Zero Gate Voltage Drain Current	I_{DSS}		1	50	μA	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	
Gate-Source Leakage Current	I_{GSS}		10	250	nA	$V_{GS} = 15\text{ V}, V_{DS} = 0\text{ V}$	
Drain-Source On-State Resistance	$R_{DS(on)}$		40	53.5	m Ω	$V_{GS} = 15\text{ V}, I_D = 33.3\text{ A}$	Fig. 4, 5, 6
			60			$V_{GS} = 15\text{ V}, I_D = 33.3\text{ A}, T_J = 150\text{ }^\circ\text{C}$	
Transconductance	g_{fs}		21		S	$V_{DS} = 20\text{ V}, I_{DS} = 33.3\text{ A}$	Fig. 7
			20			$V_{DS} = 20\text{ V}, I_{DS} = 33.3\text{ A}, T_J = 150\text{ }^\circ\text{C}$	
Input Capacitance	C_{iss}		2900		pF	$V_{GS} = 0\text{ V}, V_{DS} = 1000\text{ V}$ $f = 100\text{ kHz}$ $V_{AC} = 25\text{ mV}$	Fig. 17, 18
Output Capacitance	C_{oss}		103				
Reverse Transfer Capacitance	C_{rss}		5				
C_{oss} Stored Energy	E_{oss}		60		μJ		Fig. 16
Turn-On Switching Energy (Body Diode FWD)	E_{ON}		339		μJ	$V_{DS} = 800\text{ V}, V_{GS} = -4\text{ V}/15\text{ V},$ $I_D = 33.3\text{ A},$ $R_{G(ext)} = 2.5\text{ }\Omega, L = 99\text{ }\mu\text{H}$	Fig. 26
Turn-Off Switching Energy (Body Diode FWD)	E_{OFF}		67				
Turn-On Delay Time	$t_{d(on)}$		13		ns	$V_{DD} = 800\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}$ $R_{G(ext)} = 2.5\text{ }\Omega, I_D = 33.3\text{ A}, L = 99$ Timing Relative to V_{DS} , Inductive Load	Fig. 27
Rise Time	t_r		18				
Turn-Off Delay Time	$t_{d(off)}$		22				
Fall Time	t_f		8				
Internal Gate Resistance	$R_{G(int)}$		3.5		Ω	$f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$	
Gate to Source Charge	Q_{gs}		35		nC	$V_{DS} = 800\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}$ $I_D = 33.3\text{ A}$ Per IEC60747-8-4 pg 21	Fig. 12
Gate to Drain Charge	Q_{gd}		27				
Total Gate Charge	Q_g		94				



Reverse Diode Characteristics ($T_c = 25^\circ\text{C}$ Unless Otherwise Specified)

Parameter	Symbol	Typ.	Max.	Unit	Test Conditions	Note
Diode Forward Voltage	V_{SD}	5.5		V	$V_{GS} = -4\text{ V}, I_{SD} = 20\text{ A}, T_J = 25^\circ\text{C}$	Fig. 8, 9, 10
		4.5			$V_{GS} = -4\text{ V}, I_{SD} = 20\text{ A}, T_J = 150^\circ\text{C}$	
Continuous Diode Forward Current	I_S		44	A	$V_{GS} = -4\text{ V}, T_c = 25^\circ\text{C}$	
Diode Pulse Current	$I_{S, pulse}$		100		$V_{GS} = -4\text{ V}, \text{Pulse Width } t_p \text{ Limited by } T_{Jmax}$	
Reverse Recovery Time	t_{rr}	11		ns	$V_{GS} = -4\text{ V}, I_{SD} = 33.3\text{ A}, V_R = 800\text{ V}$ $dif/dt = 9890\text{ A}/\mu\text{s}$	
Reverse Recovery Charge	Q_{rr}	323		nC		
Peak Reverse Recovery Current	I_{rrm}	52		A		
Reverse Recovery Time	t_{rr}	17		ns	$V_{GS} = -4\text{ V}, I_{SD} = 33.3\text{ A}, V_R = 800\text{ V}$ $dif/dt = 1815\text{ A}/\mu\text{s}$	
Reverse Recovery Charge	Q_{rr}	150		nC		
Peak Reverse Recovery Current	I_{rrm}	16		A		

Thermal Characteristics

Parameter	Symbol	Typ.	Unit	Test Conditions	Note
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.46	$^\circ\text{C}/\text{W}$		Fig. 21
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	40			



Typical Performance

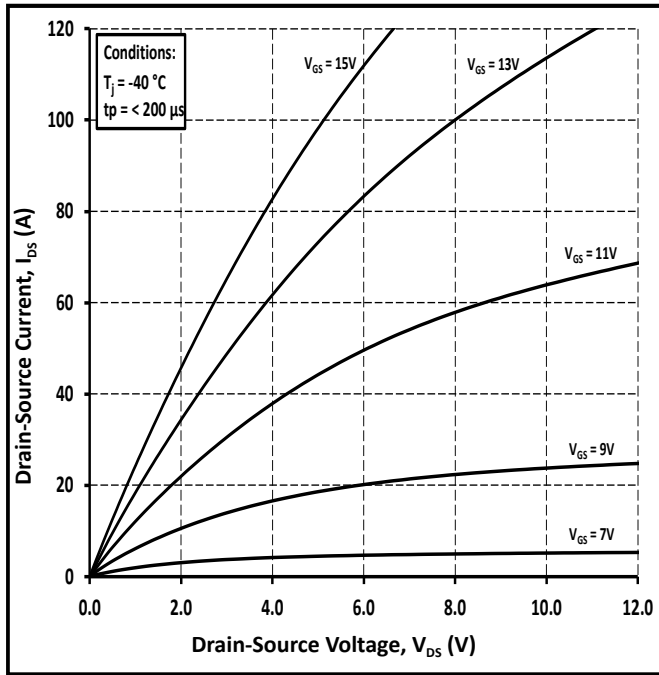


Figure 1. Output Characteristics $T_j = -40\text{ }^\circ\text{C}$

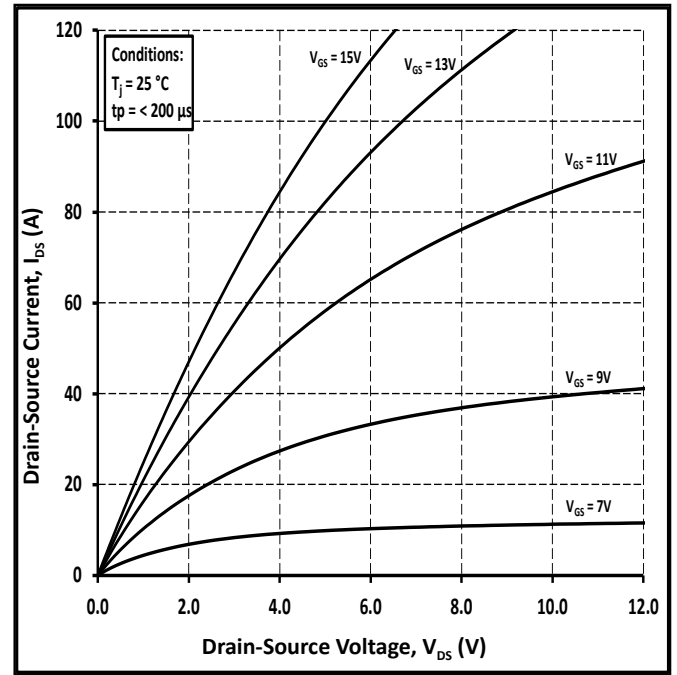


Figure 2. Output Characteristics $T_j = 25\text{ }^\circ\text{C}$

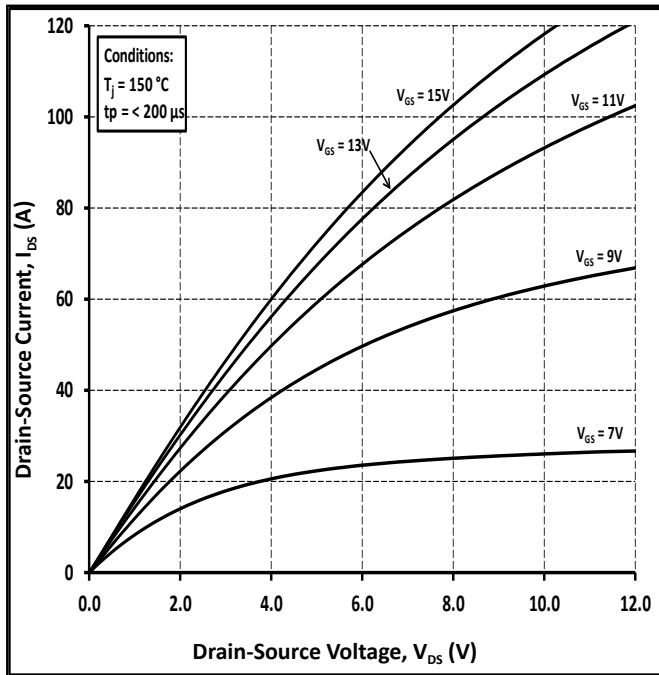


Figure 3. Output Characteristics $T_j = 150\text{ }^\circ\text{C}$

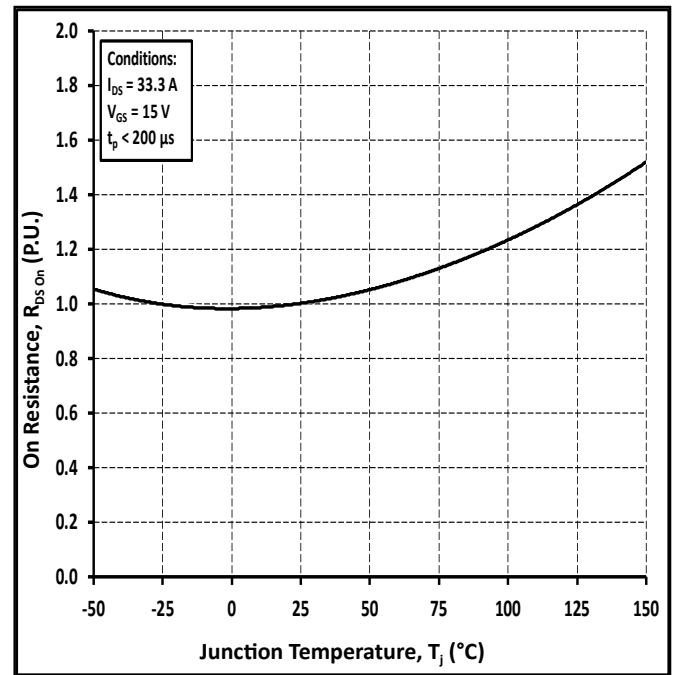


Figure 4. Normalized On-Resistance vs Temperature



Typical Performance

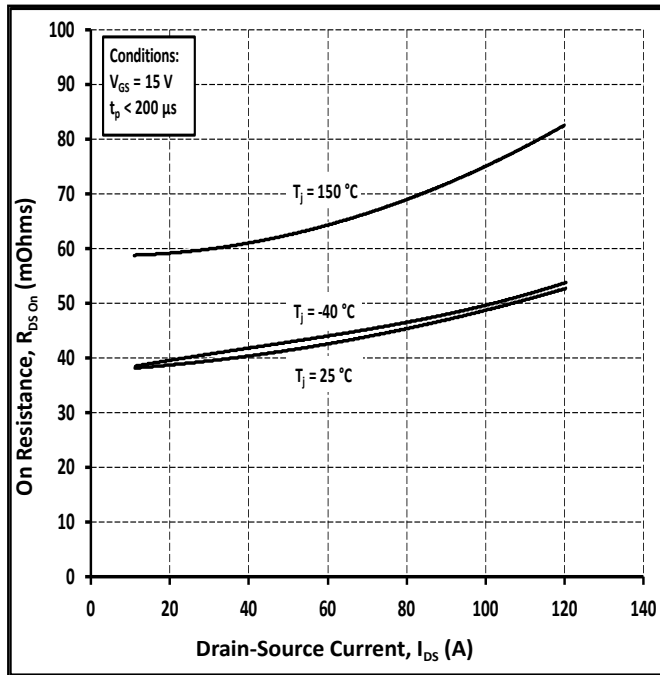


Figure 5. On-Resistance vs Drain Current for Various Temperatures

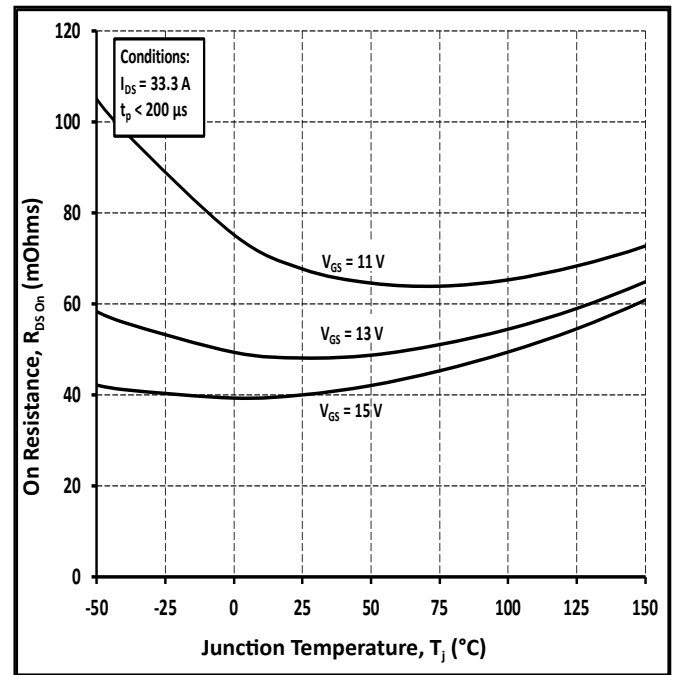


Figure 6. On-Resistance vs Temperature for Various Gate Voltage

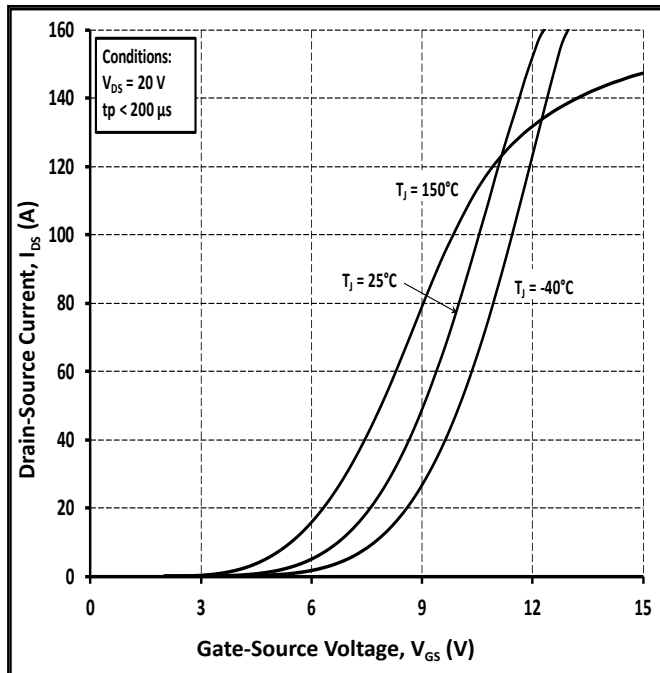


Figure 7. Transfer Characteristic for Various Junction Temperatures

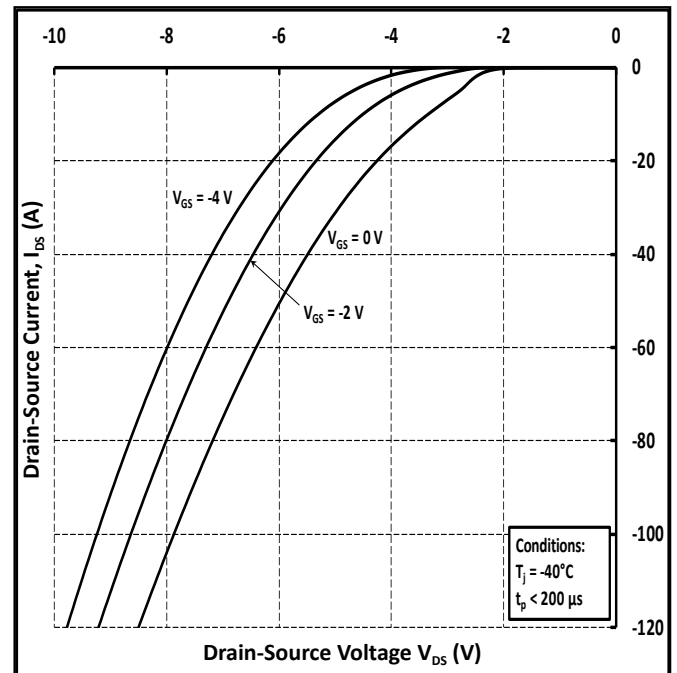


Figure 8. Body Diode Characteristic at -40 °C

Typical Performance

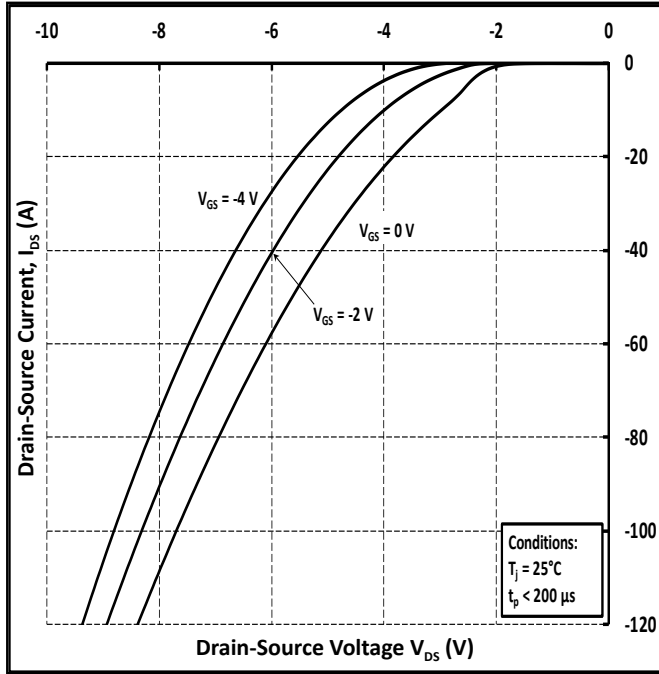


Figure 9. Body Diode Characteristic at 25 °C

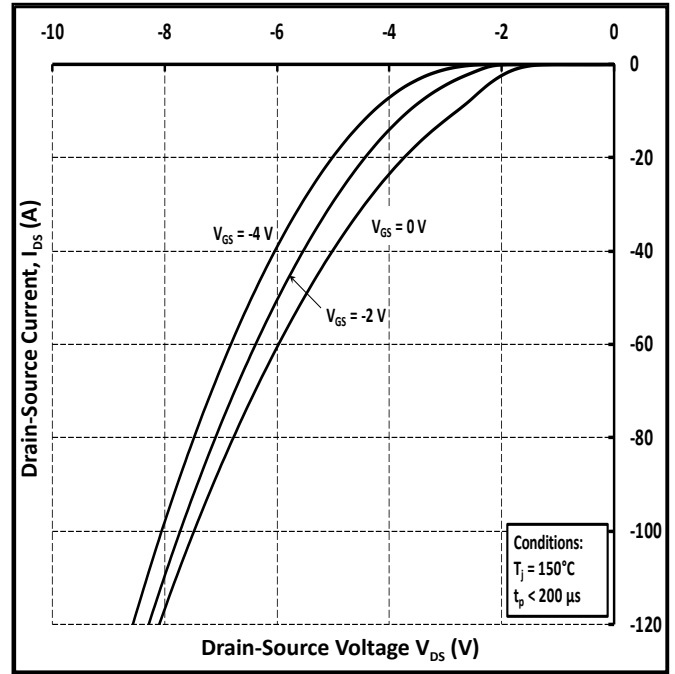


Figure 10. Body Diode Characteristic at 150 °C

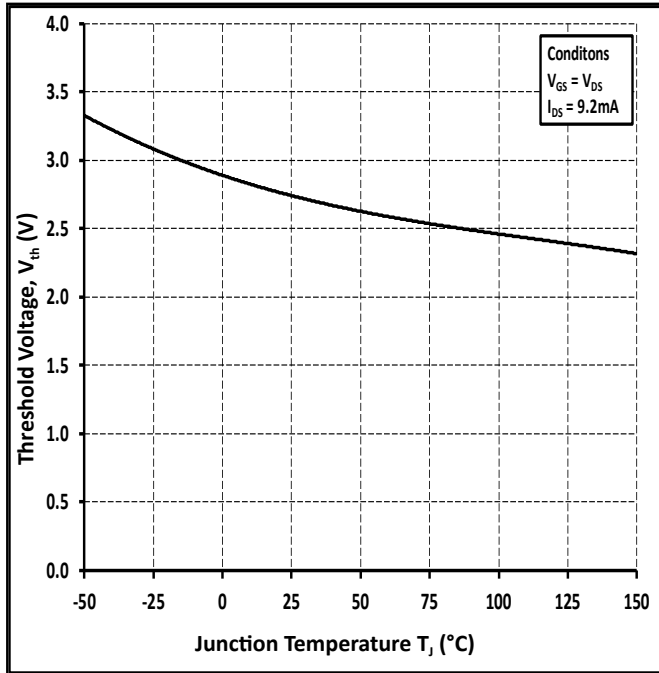


Figure 11. Threshold Voltage vs Temperature

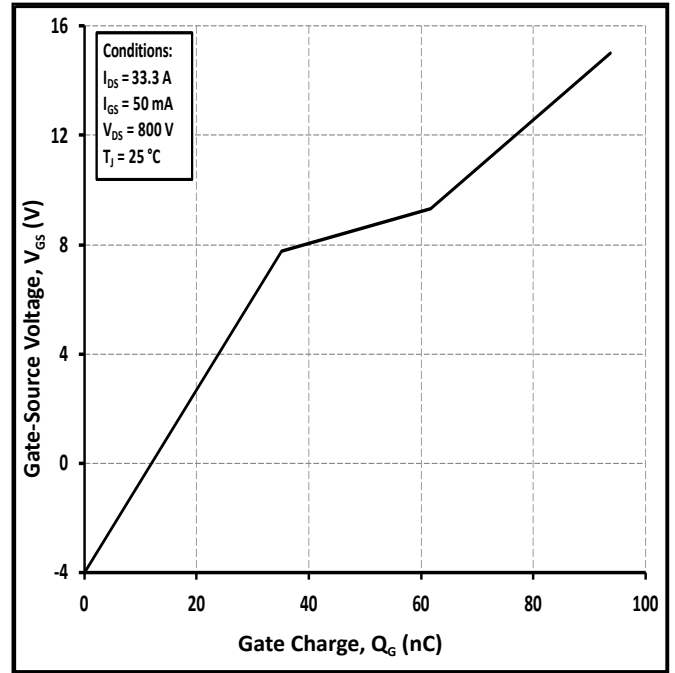


Figure 12. Gate Charge Characteristic

Typical Performance

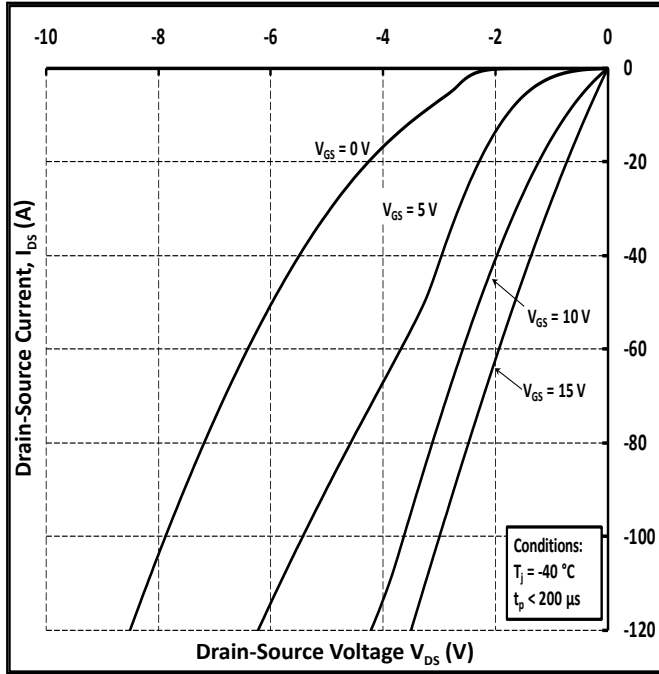


Figure 13. 3rd Quadrant Characteristic at $-40\text{ }^{\circ}\text{C}$

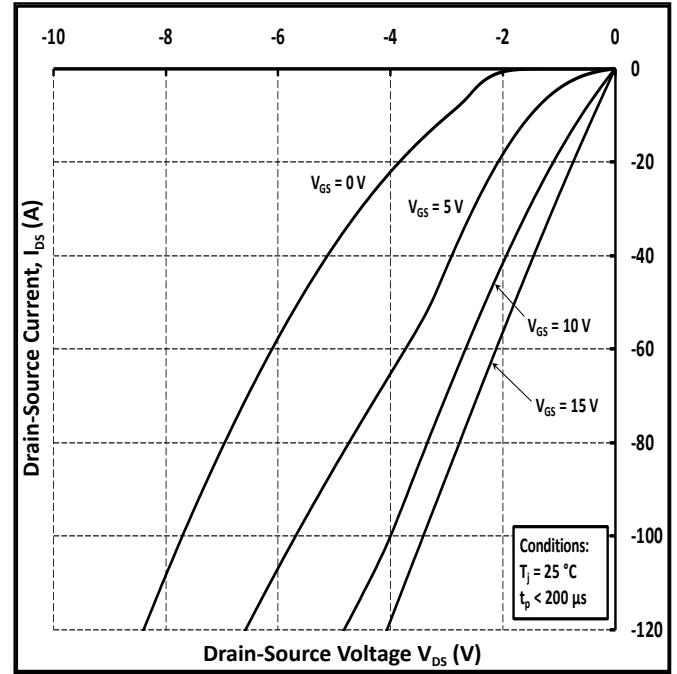


Figure 14. 3rd Quadrant Characteristic at $25\text{ }^{\circ}\text{C}$

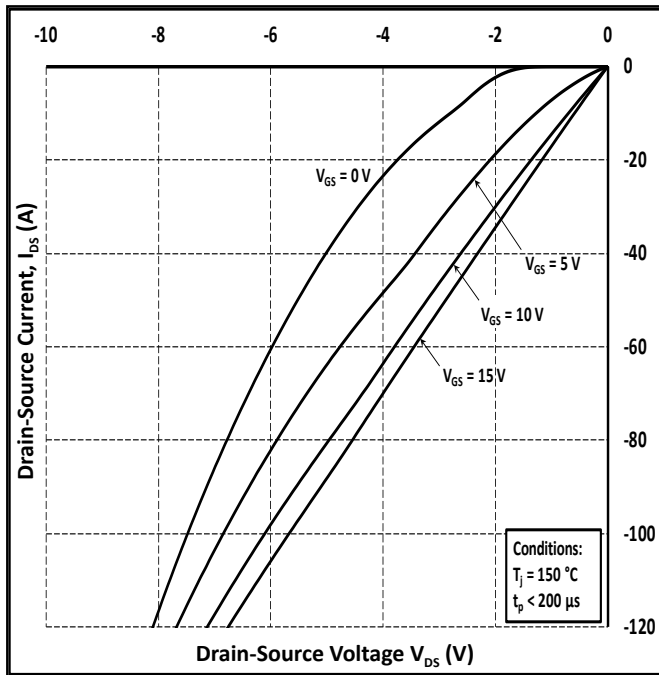


Figure 15. 3rd Quadrant Characteristic at $150\text{ }^{\circ}\text{C}$

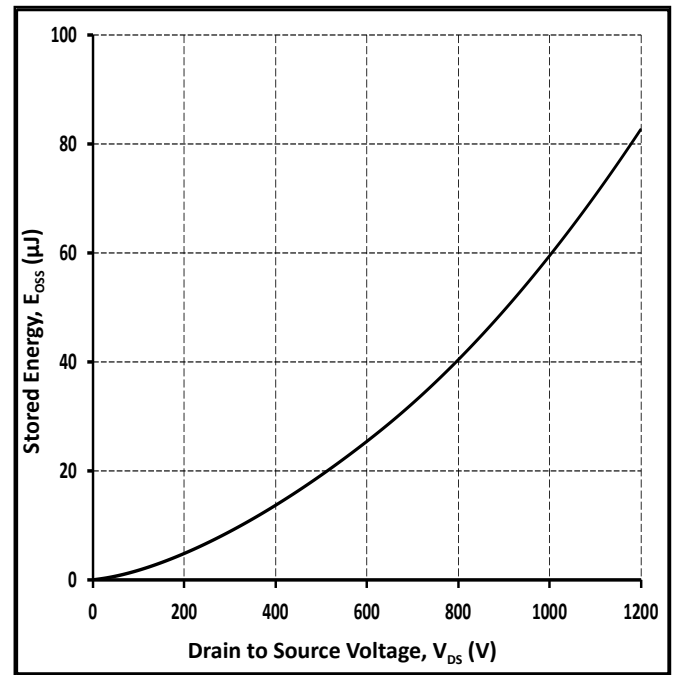


Figure 16. Output Capacitor Stored Energy

Typical Performance

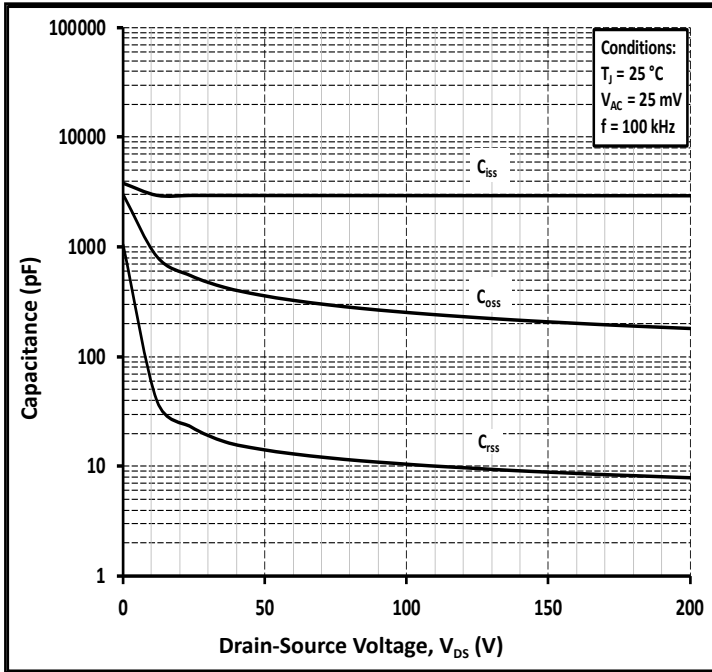


Figure 17. Capacitances vs Drain-Source Voltage (0-200 V)

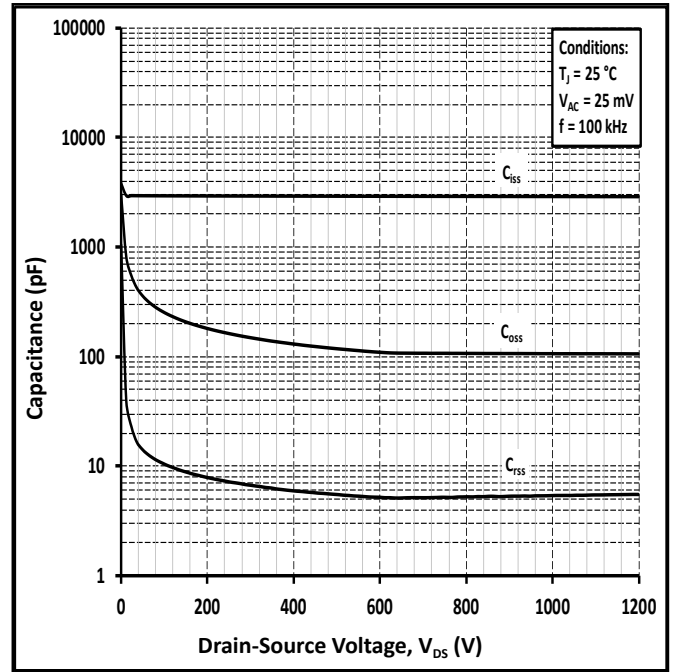


Figure 18. Capacitances vs Drain-Source Voltage (0-1200 V)

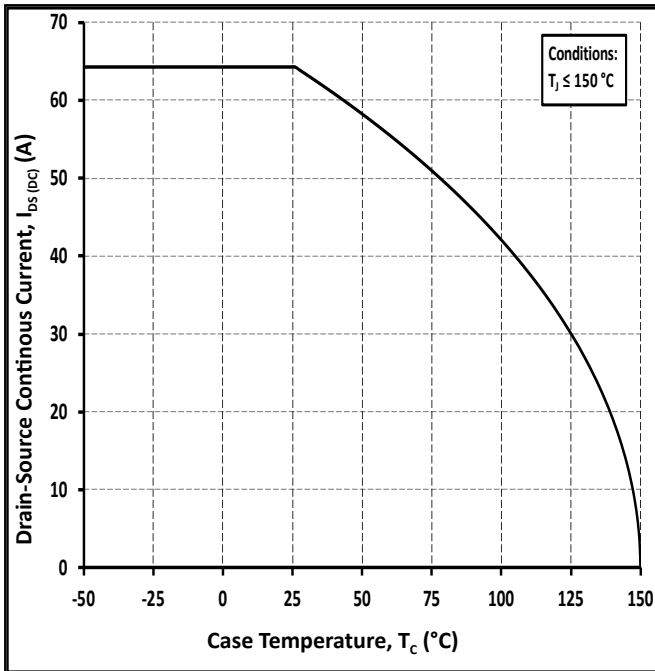


Figure 19. Continuous Drain Current Derating vs Case Temperature

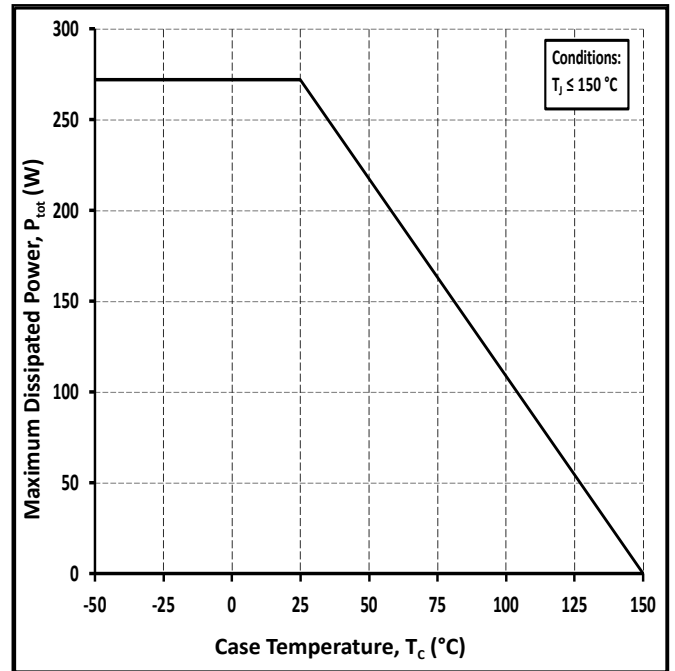


Figure 20. Maximum Power Dissipation Derating vs Case Temperature



Typical Performance

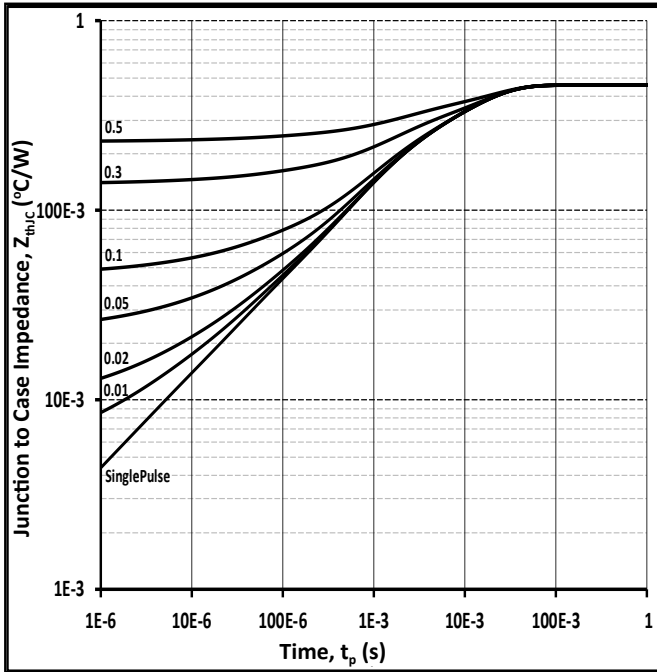


Figure 21. Transient Thermal Impedance (Junction - Case)

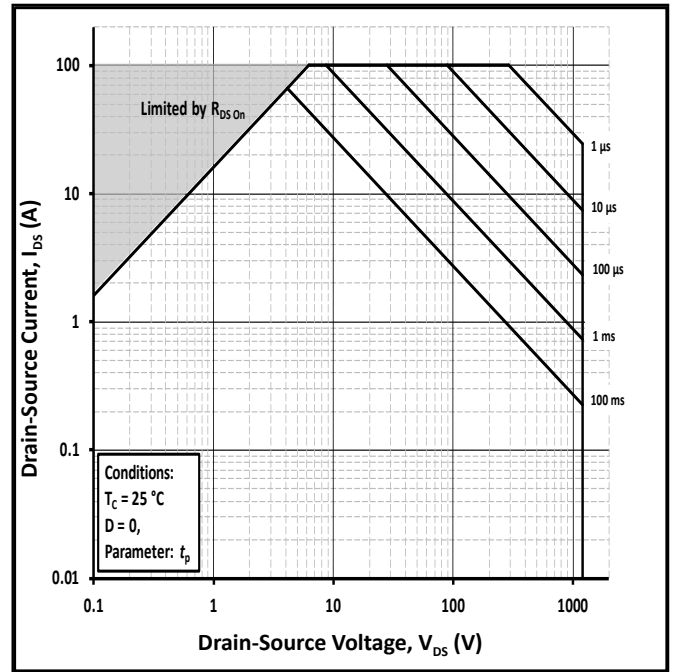


Figure 22. Safe Operating Area

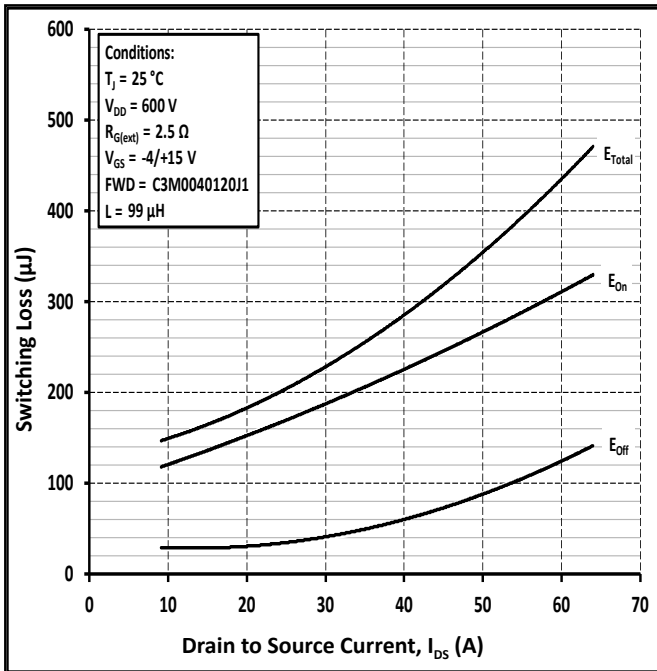


Figure 23. Clamped Inductive Switching Energy vs Drain Current ($V_{DD} = 600\text{ V}$)

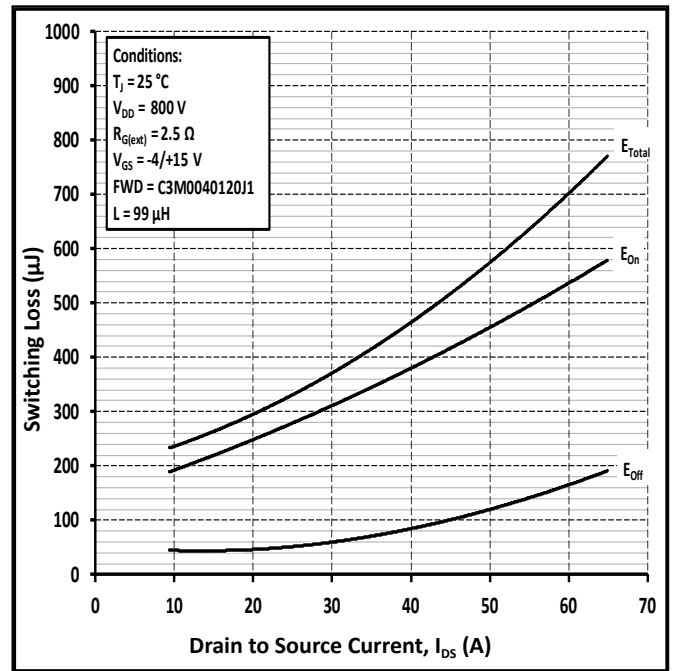


Figure 24. Clamped Inductive Switching Energy vs Drain Current ($V_{DD} = 800\text{ V}$)



Typical Performance

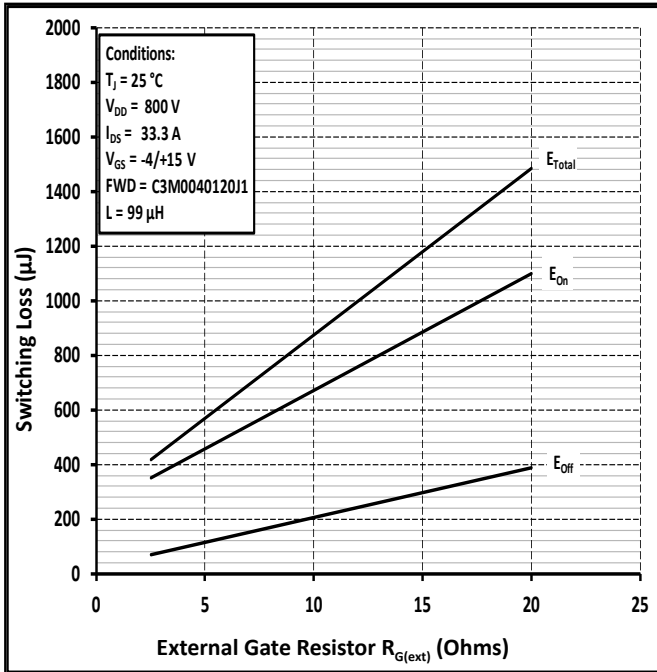


Figure 25. Clamped Inductive Switching Energy vs $R_{G(ext)}$

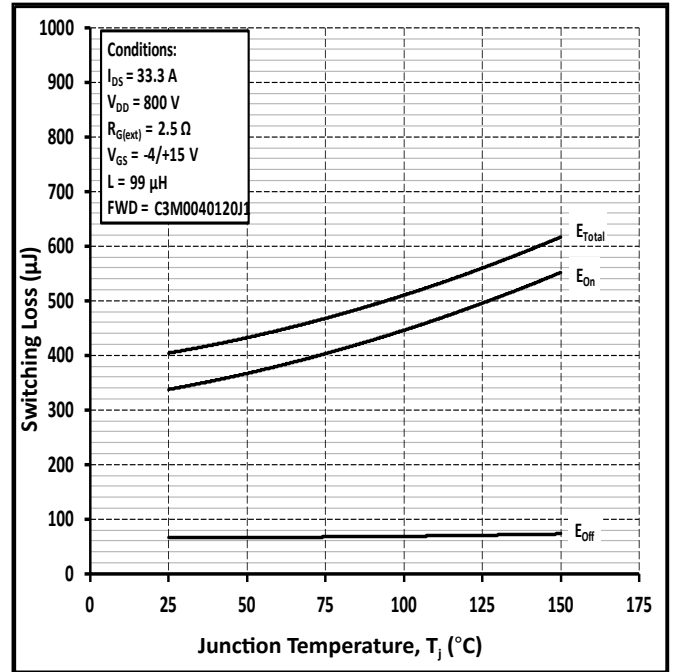


Figure 26. Clamped Inductive Switching Energy vs Temperature

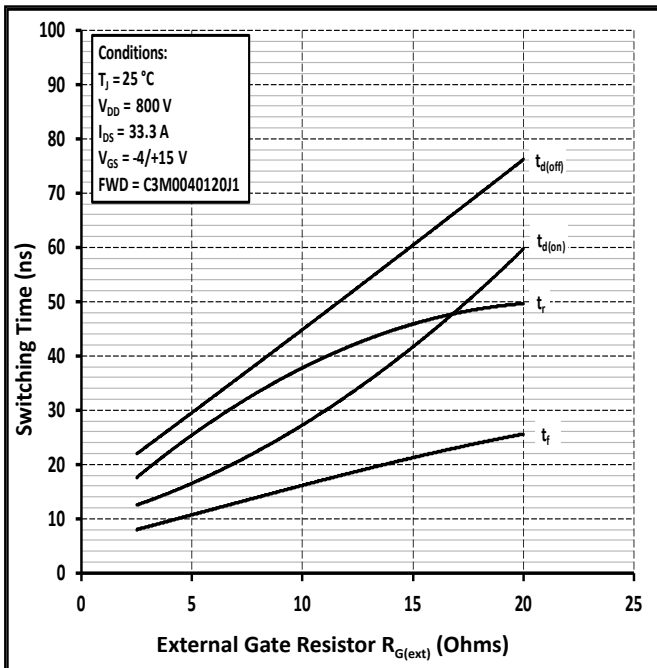


Figure 27. Switching Times vs $R_{G(ext)}$

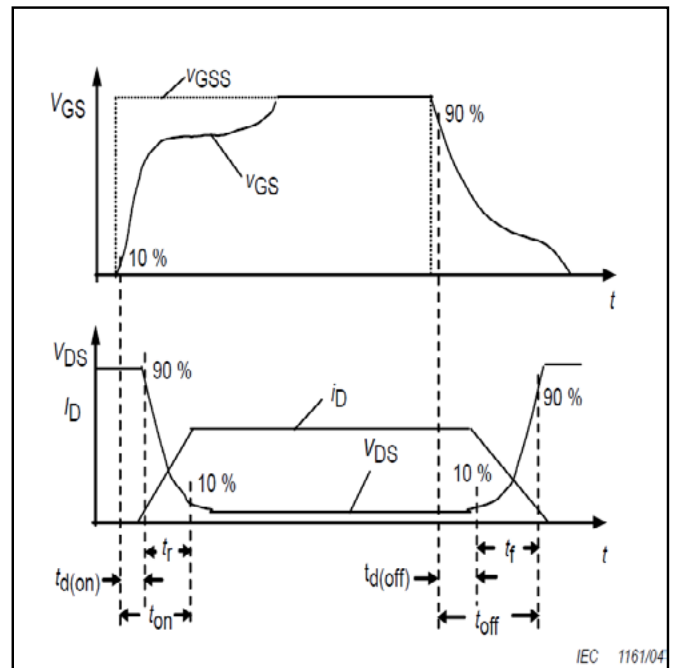


Figure 28. Switching Times Definition



Test Circuit Schematic

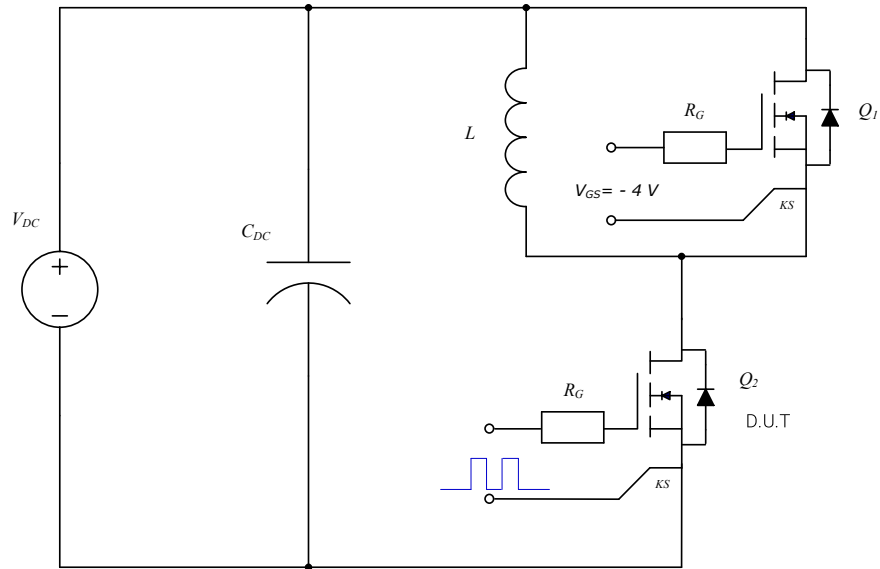


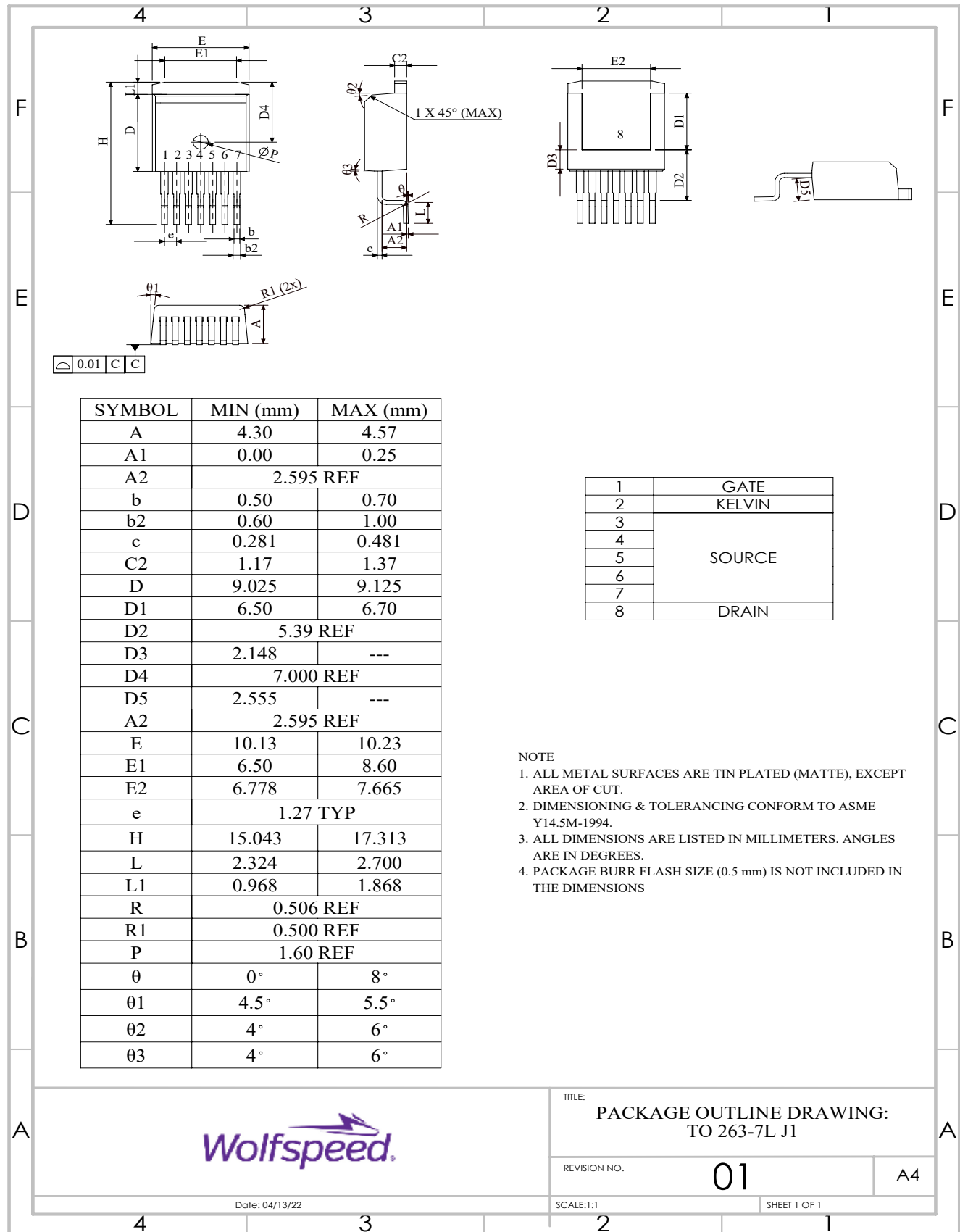
Figure 29. Clamped Inductive Switching Waveform Test Circuit

Note (3): Turn-off and Turn-on switching energy and timing values measured using SiC MOSFET body diode as shown above.



Package Dimensions

Package: TO-263-7L XL



TITLE:
PACKAGE OUTLINE DRAWING:
TO 263-7L J1

REVISION NO. **01** A4

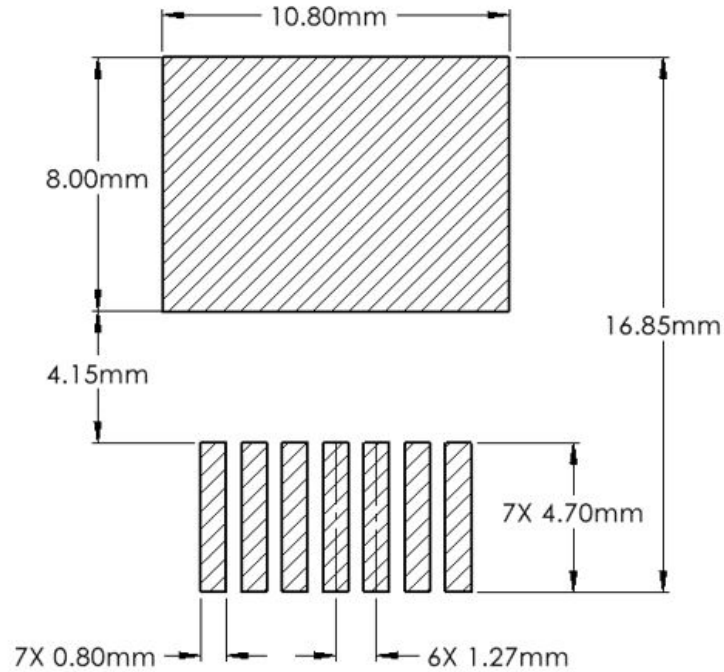
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SHEET 1 OF 1



Recommended Solder Pad Layout



Revision History

Current Revision	Date of Release	Description of Changes
0	October-2021	Initial Release
1	N/A	Not Released
2	November-2023	Updated Wolfspeed branding, package drawing, package image, solder pad layout, added Rev history, Table 1 layout revised



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